

Substitute for form 1449/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
	1.	4514895	5/7/1985	Nishimura, Tadashi
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	4.	5417897	5/23/1995	Asakawa, Stuart D. ; McClelland, Paul H. ; Tappon, Ellen R. ; Vandepoll, Richard R. ; Trueba, Kenneth E. ; Chen, Chien Hua
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	6.	5466908	11/14/1995	Hosoya, Kimio ; Teruya, Yoshihiro ; Kobayashi, Yasushi
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	14.	6093934	7/25/2000	Yamazaki, Shunpei ; Teramoto, Satoshi ; Koyama, Jun ; Ogata, Yasushi ; Hayakawa, Masahiko ; Osame, Mitsuaki ; Ohtani, Hisashi ; Hamatani, Toshiji
	15.	6117301	9/12/2000	Freudenberg, Renate ; Zielonka, Andreas
	16.	6198141	3/6/2001	Yamazaki, Shunpei ; Ohtani, Hisashi ; Fukunaga, Takeshi
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	18.	6255146	7/3/2001	Shimizu, Satoshi ; Ueno, Shuichi ; Maeda, Shigenobu ; Ipposhi, Takashi
	19.	6274488	8/14/2001	Talwar, Somit ; Wang, Yun
	20.	6341042	1/22/2002	Matsunaka, Shigeki ; Fujihara, Atsushi ; Kakuno, Tsutomu
	21.	6348990	2/19/2002	Igasaki, Yasunori ; Yoshida, Narihiro ; Toyoda, Haruyoshi ; Hara, Tsutomu
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	23.	6358784	3/19/2002	Zhang, Hongyong ; Yamazaki, Shunpei ; Takemura, Yasuhiko
	24.	6388386	5/14/2002	Kunii, Masafumi ; Takatoku, Makoto ; Mano, Michio

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	49.	6577380	6/10/2003	Sposili, Robert S. ; Farmiga, Nestor O. ; Jain, Kanti

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	61.	6908835	6/21/2005	Sposili, Robert S. ; Im, James S.
	62.	6961117	11/1/2005	Im, James S.
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Exam Initial	No.	Document No.	Publication Date	Applicant(s)
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	65.	7217605	5/15/2007	Kawasaki, Ritsuko ; Nakajima, Setsuo
	66.	7259081	8/21/2007	Im, James S.
	67.	7297982	11/20/2007	Suzuki, Kenkichi ; Nagata, Tetsuya ; Takahashi, Michiko ; Saito, Masakazu ; Ogino, Toshio ; Miyano, Masanobu
	68.	7300858	11/27/2007	Im, James S.
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	70.	7341928	3/11/2008	Im, James S.
	71.	20020083557	7/4/2002	Jung, Yun Ho
	72.	20020096680	7/25/2002	Sugano, Yukiyasu ; Fujino, Masahiro ; Mano, Michio ; Asano, Akihiko ; Ino, Masumitsu ; Urazono, Takenobu ; Takatoku, Makoto
	73.	20020119609	8/29/2002	Hatano, Mutsuko ; Yamaguchi, Shinya ; Kimura, Yoshinobu ; Park, Seong Kee
	74.	20020151115	10/17/2002	Nakajima, Hideharu ; Negoro, Yoichi ; Usui, Setsuo
	75.	20030003242	1/2/2003	Voutsas, Apostolos
	76.	20030006221	1/9/2003	Hong, Minghui ; Ye, Kaidong ; An, Chengwu ; Liu, Da Ming

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	79.	20030068836	4/10/2003	Hongo, Mikio ; Uto, Sachio ; Nomoto, Mineo ; Nakata, Toshihiko ; Hatano, Mutsuko ; Yamaguchi, Shinya ; Ohkura, Makoto
	80.	20030119286	6/26/2003	Im, James, S. ; Sposili, Robert, S. ; Crowder, Mark, A.
	81.	20030148565	8/7/2003	Yamanaka, Hideo
	82.	20030194613	10/16/2003	Voutsas, Apostolos, T. ; Crowder, Mark, A. ; Mitiani, Yasuhiro
	83.	20040127066	7/1/2004	Jung, Yun Ho
	84.	20040140470	7/22/2004	Kawasaki, Ritsuko ; Kasahara, Kenji ; Ohtani, Hisashi
	85.	20040169176	9/2/2004	Peterson, Paul, E. ; Stasiak, James
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	89.	20050059265	3/17/2005	Im, James

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	91.	20050142450	6/30/2005	Jung, Yun
	92.	20050142451	6/30/2005	You, JaeSung
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	94.	20060030164	2/9/2006	Im, James
	95.	20060102901	5/18/2006	Im, James ; van der Wilt, Paul
	96.	20060125741	6/15/2006	Tanaka, Masahiro ; Matsuura, Toshiyuki ; Murakami, Hajime ; Akimoto, Hajime
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	99.	20070007242	1/11/2007	Im, James
	100.	20070020942	1/25/2007	Im, James
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	102.	20070108472	5/17/2007	Jeong, Jae, Kyeong ; Shin, Hyun, Soo ; Kwon, Se, Yeoul ; Mo, Yeon, Gon
	103.	20070111349	5/17/2007	Im, James

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	104.	20070215942	9/20/2007	Chen, Po Chu ; Ho, King Yuan

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Application Number	10/524,809
Filing Date	02/15/2005
Inventor(s)	James S. Im
Art Unit	2895
Examiner Name	Fernando L. Toledo
Attorney Docket Number	070050.2721

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